

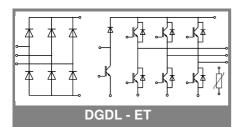
SEMITOP<sup>®</sup>3

#### 3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SK 15 DGDL 12T4 ET

Target Data

#### Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor
- 1)  $V_{CE,sat}$ ,  $V_F$  = chip level value



Absolute	Maximum Ratings	Ts = 25 °C, un	ess otherwise	specified
Symbol  Conditions		1 <b>v</b>	Values	
-	erter,Chopper			Units
V <sub>CES</sub>		-	200	V
	T <sub>s</sub> = 25 (70) °C		7 (21)	Å
I <sub>C</sub>	3 ,	2	45	
I <sub>CRM</sub>	$I_{CRM}$ = 3 x $I_{Cnom}$ , $t_p$ = 1 ms		± 20	
V <sub>GES</sub> T			-40 +175	
Т <sub>ј</sub>		-40	+1/5	°C
Diode - Inv	verter,Chopper			
I <sub>F</sub>	T <sub>s</sub> = 25 (70) °C	2	21 (17)	
I <sub>FRM</sub>	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$		45	
T <sub>i</sub>		-40	-40 +150	
Rectifier				
V <sub>RRM</sub>	I		600	V
I <sub>F</sub>	T <sub>s</sub> = 70 °C		28	
I <sub>FSM</sub> / I <sub>TSM</sub>	$t_p = 10 \text{ ms}$ , sin 180 °, $T_i = 25 \text{ °C}$		220	
$I_t^2$	$t_{p} = 10 \text{ ms}$ , sin 180 °, $T_{i} = 25 \text{ °C}$		240	
			240 A <sup>2</sup> -40 +175 °C	
T <sub>j</sub>	<b>T 1 1 1</b>			
T <sub>sol</sub>	Terminals, 10 s		260 °C -40 +125 °C	
T <sub>stg</sub>			-40 +125	
V <sub>isol</sub>	AC, 1 min. / 1 s	250	2500 / 3000 V	
Character	istics	Ts = 25 °C, un	ess otherwise	specified
Symbol	Conditions	min.	typ. max.	Units
IGBT - Inv	erter			
V <sub>CEsat</sub>	I <sub>C</sub> = 15 A, T <sub>i</sub> = 25 (150) °C	1,8	5 (2,25) 2,05 (2,4	5) V
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_{C} = 0,5 \text{ mA}$	5	5,8 6,5	V
V <sub>CE(TO)</sub>	T <sub>j</sub> = 25 °C (150) °C	1	,1 (1) 1,3 (1,2)	) V
r <sub>T</sub>	T <sub>i</sub> = 25 °C (150) °C	50	(83,3)	mΩ
C <sub>ies</sub>	V <sub>CE</sub> = 25 V <sub>GE</sub> = 0 V, f = 1 MHz		0,9	nF
C <sub>oes</sub>	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$	(	),08	_
C <sub>res</sub>				nF
_	V <sub>CE</sub> = 25 V <sub>GE</sub> = 0 V, f = 1 MHz	0	,055	n⊦ nF
R <sub>th(i-s)</sub>	V <sub>CE</sub> = 25 V <sub>GE</sub> = 0 V, f = 1 MHz per IGBT		,055 I,65	
R <sub>th(j-s)</sub> t <sub>d(op)</sub>	per IGBT			nF
t <sub>d(on)</sub>	per IGBT under following conditions		,65	nF K/W
t <sub>d(on)</sub> t <sub>r</sub>	per IGBT under following conditions $V_{CC} = 600 \text{ V}, \text{ V}_{GE} = \pm 15 \text{ V}$		1,65 16	nF K/W ns
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub>	per IGBT under following conditions $V_{CC} = 600 V, V_{GE} = \pm 15 V$ $I_C = 15 A, T_i = 150 °C$		1,65 16 14	nF K/W ns ns
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	per IGBT under following conditions $V_{CC} = 600 \text{ V}, \text{ V}_{GE} = \pm 15 \text{ V}$		1,65 16 14 273 85	nF K/W ns ns ns
$\begin{array}{l} t_{d(on)} \\ t_{r} \\ t_{d(off)} \\ t_{f} \\ E_{on} \end{array}$	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 \text{ °C}$ $R_{Gon} = R_{Goff} = 16 \Omega$		1,65 16 14 273 85 0,82	nF K/W ns ns ns ms mJ
$\begin{array}{l} t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \\ E_{on} \\ E_{off} \end{array}$	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 ^{\circ}\text{C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load		1,65 16 14 273 85	nF K/W ns ns ns ns
$\begin{array}{l} t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \\ E_{on} \\ E_{off} \end{array}$	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 \text{ °C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load verter,Chopper		1,65 16 14 273 85 0,82 1,52	nF K/W ns ns ns mJ mJ
$\begin{array}{l} t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \\ E_{on} \\ E_{off} \end{array} \\ \hline \textbf{Diode - Inv} \\ V_F = V_{EC} \end{array}$	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 ^{\circ}\text{C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load <b>verter,Chopper</b> $I_F = 15 \text{ A}, T_j = 25(150) ^{\circ}\text{C}$	2,38	1,65 16 14 273 85 0,82 1,52 3 (2,44) 2,71 (2,7)	nF K/W ns ns ns mJ mJ 7) V
	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 ^{\circ}\text{C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load <b>verter,Chopper</b> $I_F = 15 \text{ A}, T_j = 25(150) ^{\circ}\text{C}$ $T_j = 25 ^{\circ}\text{C} (150) ^{\circ}\text{C}$	2,30	1,65 16 14 273 85 0,82 1,52 3 (2,44) 2,71 (2,7) 3 (0,9) 1,5 (1,1)	<pre>nF K/W ns ns ns mJ mJ 7) V V </pre>
$\begin{array}{l} t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \\ E_{on} \\ E_{off} \end{array} \\ \hline \textbf{Diode - Inv} \\ V_F = V_{EC} \end{array}$	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 ^{\circ}\text{C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load <b>verter,Chopper</b> $I_F = 15 \text{ A}, T_j = 25(150) ^{\circ}\text{C}$	2,30	1,65 16 14 273 85 0,82 1,52 3 (2,44) 2,71 (2,72 3 (0,9) 1,5 (1,1) (102,7) 80,6	nF           K/W           ns           ns           ns           mJ           mJ           7)         V           γ           πΩ
	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 ^{\circ}\text{C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load <b>verter,Chopper</b> $I_F = 15 \text{ A}, T_j = 25(150) ^{\circ}\text{C}$ $T_j = 25 ^{\circ}\text{C} (150) ^{\circ}\text{C}$	2,3i 1, 72	1,65 16 14 273 85 0,82 1,52 3 (2,44) 2,71 (2,7) 3 (0,9) 1,5 (1,1)	nF           K/W           ns           ns           ns           mJ           mJ           v           V           V           mΩ
	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 \text{ °C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load <b>verter,Chopper</b> $I_F = 15 \text{ A}, T_j = 25(150) \text{ °C}$ $T_j = 25 \text{ °C} (150) \text{ °C}$ $T_j = 25 \text{ °C} (150) \text{ °C}$ per diode	2,3i 1, 72	1,65 16 14 273 85 0,82 1,52 3 (2,44) 2,71 (2,77 3 (0,9) 1,5 (1,1) (102,7) 80,6 (111,3) 2,34	nF           K/W           ns           ns           ns           mJ           mJ           K/W
	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 \text{ °C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load <b>verter,Chopper</b> $I_F = 15 \text{ A}, T_j = 25(150) \text{ °C}$ $T_j = 25 \text{ °C} (150) \text{ °C}$ $T_j = 25 \text{ °C} (150) \text{ °C}$ per diode under following conditions	2,3i 1,: 72	1,65 16 14 273 85 ),82 1,52 3 (2,44) 2,71 (2,77 3 (0,9) 1,5 (1,1) (102,7) 80,6 (111,3) 2,34 28	nF           K/W           ns           ns           ns           mJ           7)         V           γ           K/W
	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 \text{ °C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load <b>verter,Chopper</b> $I_F = 15 \text{ A}, T_j = 25(150) \text{ °C}$ $T_j = 25 \text{ °C} (150) \text{ °C}$ $T_j = 25 \text{ °C} (150) \text{ °C}$ per diode under following conditions $I_F = 15 \text{ A}, V_R = V$	2,3i 1, 72	1,65 16 14 273 85 0,82 1,52 3 (2,44) 2,71 (2,77 3 (0,9) 1,5 (1,1) (102,7) 80,6 (111,3) 2,34 28 0,3	nF           K/W           ns           ns           mJ           mJ           K/W           K/W
	per IGBT under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}, T_j = 150 \text{ °C}$ $R_{Gon} = R_{Goff} = 16 \Omega$ inductive load <b>verter,Chopper</b> $I_F = 15 \text{ A}, T_j = 25(150) \text{ °C}$ $T_j = 25 \text{ °C} (150) \text{ °C}$ $T_j = 25 \text{ °C} (150) \text{ °C}$ per diode under following conditions	2,3i 1, 72	1,65 16 14 273 85 ),82 1,52 3 (2,44) 2,71 (2,77 3 (0,9) 1,5 (1,1) (102,7) 80,6 (111,3) 2,34 28	nF           K/W           ns           ns           mJ           mJ           V           V           K/W           K/W

Mounting torque

I<sub>F</sub> = 15 A, T<sub>i</sub> = 25() °C

5 %, T<sub>r</sub> = 25 (100 ) °C

T<sub>i</sub> = 150 °C

T<sub>i</sub> = 150 °C

per diode

**Diode - Rectifier** 

**Temperatur sensor** 

Mechanical data

 $V_{F}$ 

r<sub>T</sub>

V<sub>(TO)</sub>

R<sub>th(j-s)</sub>

 $\mathsf{R}_{\mathsf{ts}}$ 

w

 $M_s$ 

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2,5

1,1

0,9

20

2

5000(493)

30

2,25

V

V

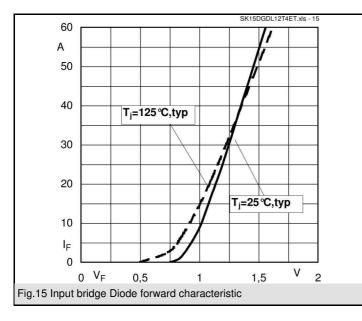
mΩ

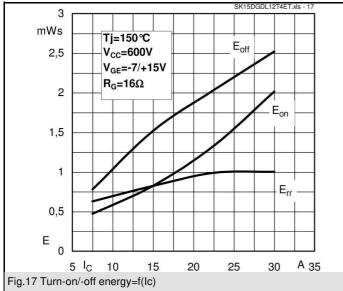
K/W

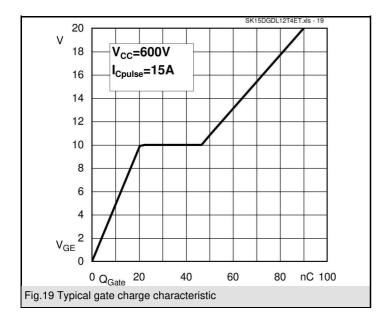
Ω

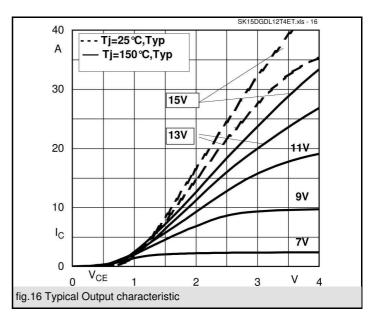
g

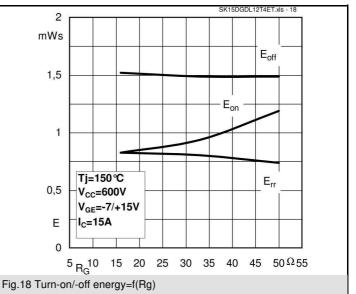
Nm

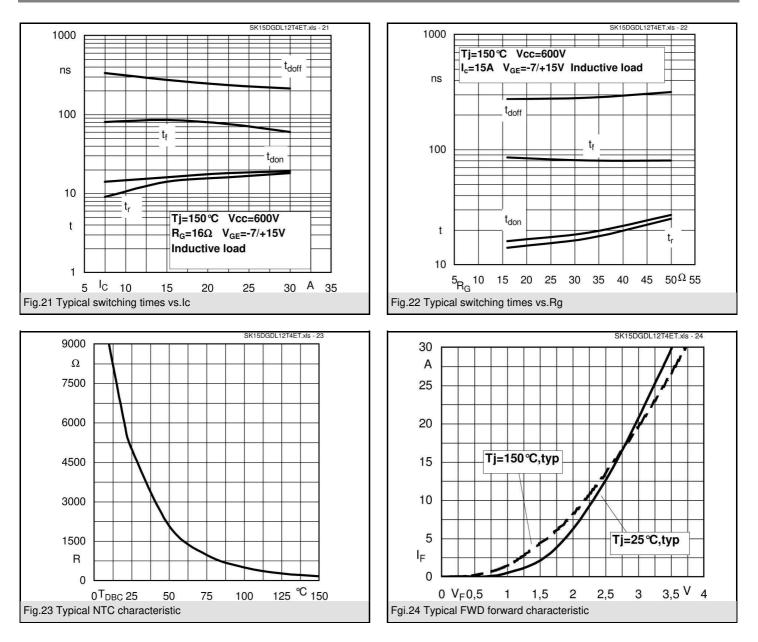


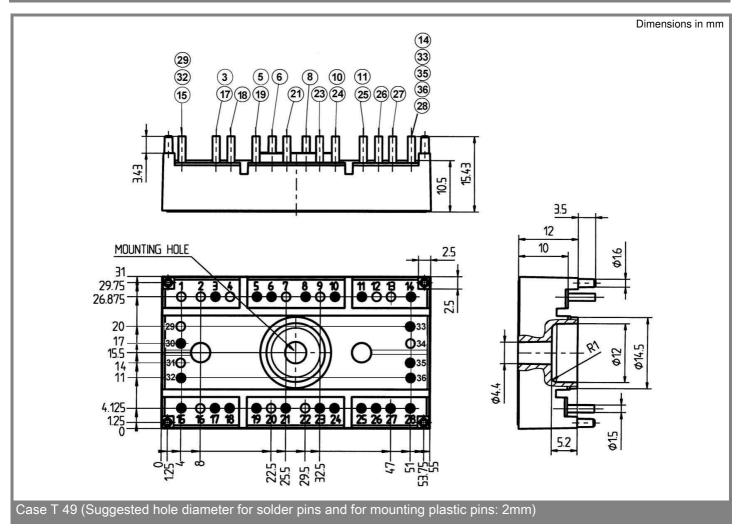


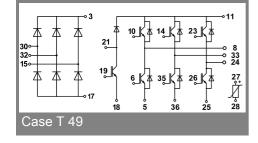












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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 F4 

 75R12KS4\_B11
 FB15R06W1E3
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 FD1000R33HE3-K
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 FD300R12KE3
 FD300R12KS4\_B5

 FD400R12KE3
 FD400R33KF2C-K
 FD401R17KF6C\_B2
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 FF100R12KS4
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 FF200R17KE3
 FF300R12KE4\_E

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 FF300R12MS4
 FF300R12MS4
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 FP10R12W1T4\_B11
 FP10R12YT3
 FP10R12YT3\_B4
 FP150R07N3E4
 FP15R12KT3

 FP15R12W2T4
 F
 FF150R12W1T4\_B11
 FF10R12YT3
 FP10R12YT3\_B4
 FP150R07N3E4
 FP15R12KT3